DS90LV011AH High Temperature 3V LVDS Differential Driver



DS90LV011AH High Temperature 3V LVDS Differential Driver General Description Features

The DS90LV011AH is an LVDS driver optimized for high data rate and low power applications. The DS90LV011AH is a current mode driver allowing power dissipation to remain low even at high frequency. In addition, the short circuit fault current is also minimized. The device is designed to support data rates in excess of 400Mbps (200MHz) utilizing Low Voltage Differential Signaling (LVDS) technology.

The device is offered in a 5-lead small outline transistor package. The LVDS outputs have been arranged for easy PCB layout. The differential driver outputs provide low EMI with its typical low output swing of 350 mV. The DS90LV011AH can be paired with its companion single line receiver, the DS90LT012AH, or with any of National's LVDS receivers, to provide a high-speed LVDS interface.

- -40°C to 125°C operating temperature range
- Conforms to TIA/EIA-644-A Standard
- >400Mbps (200MHz) switching rates
- 700 ps (100 ps typical) maximum differential skew
- 1.5 ns maximum propagation delay
- Single 3.3V power supply
- ±350 mV differential signaling
- Power Off Protection (outputs in TRI-STATE)
- Pinout simplifies PCB layout
- Low power dissipation (23 mW @ 3.3V typical)
- SOT-23 5-lead package
- Pin compatible with SN65LVDS1

Connection Diagram



Absolute Maximum Ratings (Note 1)

If Military/Aerospace specified devices are required, please contact the National Semiconductor Sales Office/ Distributors for availability and specifications.

Supply Voltage (V _{DD})	-0.3V to +4V
LVCMOS input voltage (TTL IN	l) -0.3V to +3.6V
LVDS output voltage (OUT±)	-0.3V to +3.9V
LVDS output short circuit curre	nt 24mA
Maximum Package Power Diss	sipation @ +25°C
MF Package	902 mW
Derate MF Package	7.22 mW/°C above +25°C
Thermal resistance (θ_{JA})	138.5°C/Watt
Storage Temperature	–65°C to +150°C
Lead Temperature Range Sold	ering
(4 sec.)	+260°C

Maximum Junction	
Temperature	+150°C
ESD Ratings	
HBM (1.5 kΩ, 100 pF)	\ge 9kV
EIAJ (0 Ω, 200 pF)	\geq 900V
CDM (0 Ω, 0 pF)	\geq 2000V
IEC direct (330 Ω, 150 pF)	$\ge 4 \text{kV}$

Recommended Operating Conditions

	Min	Тур	Max	Units
Supply Voltage (V _{DD})	3.0	3.3	3.6	V
Temperature (T _A)	-40	+25	+125	°C

Electrical Characteristics

Over Supply Voltage and Operating Temperature ranges, unless otherwise specified. (Notes 2, 3, 8)

Symbol	Parameter	Conditions		Pin	Min	Тур	Max	Units
V _{OD}	Output Differential Voltage	R _L = 100Ω		OUT+,	250	350	450	mV
ΔV_{OD}	V _{OD} Magnitude Change	(Figure 1 and Figure 2)		OUT-		3	35	mV
V _{os}	Offset Voltage	$R_L = 100\Omega$		1	1.125	1.22	1.375	V
ΔV_{OS}	Offset Magnitude Change	(Figure 1)			0	1	25	mV
I _{OFF}	Power-off Leakage	V _{OUT} = 3.6V c	or GND, V _{DD} = 0V	1		±1	±10	μA
I _{OS}	Output Short Circuit Current (Note 4)	V_{OUT+} and $V_{OUT-} = 0V$				-6	-24	mA
I _{OSD}	Differential Output Short Circuit Current (Note 4)	V _{OD} = 0V				-5	-12	mA
C _{OUT}	Output Capacitance			1		3		pF
V _{IH}	Input High Voltage			TTL IN	2.0		V _{DD}	V
V _{IL}	Input Low Voltage]	GND		0.8	V
I _{IH}	Input High Current	V _{IN} = 3.3V or 2.4V]		±2	±10	μA
IIL	Input Low Current	V _{IN} = GND or 0.5V]		±1	±10	μA
V _{CL}	Input Clamp Voltage	I _{CL} = -18 mA		1	-1.5	-0.6		V
CIN	Input Capacitance			1		3		pF
I _{DD}	Power Supply Current	No Load	$V_{IN} = V_{DD}$ or GND	V _{DD}		5	8	mA
		$R_L = 100\Omega$]			7	10	mA

Switching Characteristics

Over Supply Voltage and Operating Temperature Ranges, unless otherwise specified. (Notes 3, 5, 6, 7)

Symbol	Parameter	Conditions	Min	Тур	Max	Units
t _{PHLD}	Differential Propagation Delay High to Low	$R_{L} = 100\Omega, C_{L} = 15 \text{ pF}$	0.3	1.0	1.5	ns
t _{PLHD}	Differential Propagation Delay Low to High	(Figure 3 and Figure 4)	0.3	1.1	1.5	ns
t _{SKD1}	Differential Pulse Skew It _{PHLD} - t _{PLHD} I (Note 9)		0	0.1	0.7	ns
t _{SKD3}	Differential Part to Part Skew (Note 10)		0	0.2	1.0	ns
t _{SKD4}	Differential Part to Part Skew (Note 11)		0	0.4	1.2	ns
t _{TLH}	Transition Low to High Time		0.2	0.5	1.0	ns
t _{THL}	Transition High to Low Time		0.2	0.5	1.0	ns
f _{MAX}	Maximum Operating Frequency (Note 12)		200	250		MHz

Note 1: "Absolute Maximum Ratings" are those values beyond which the safety of the device cannot be guaranteed. They are not meant to imply that the devices should be operated at these limits. The table of "Electrical Characteristics" specifies conditions of device operation.

Note 2: Current into device pins is defined as positive. Current out of device pins is defined as negative. All voltages are referenced to ground except V_{OD} . **Note 3:** All typicals are given for: $V_{DD} = +3.3V$ and $T_A = +25$ °C.

Switching Characteristics (Continued)

Note 4: Output short circuit current (I_{OS}) is specified as magnitude only, minus sign indicates direction only.

Note 5: These parameters are guaranteed by design. The limits are based on statistical analysis of the device performance over PVT (process, voltage, temperature) ranges.

Note 6: C_L includes probe and fixture capacitance.

Note 7: Generator waveform for all tests unless otherwise specified: f = 1 MHz, Z_0 = 50 Ω , $t_r \le 1$ ns, $t_f \le 1$ ns (10%-90%).

Note 8: The DS90LV011AH is a current mode device and only function with datasheet specification when a resistive load is applied to the drivers outputs.

Note 9: t_{SKD1}, lt_{PHLD} - t_{PLHD}I, is the magnitude difference in differential propagation delay time between the positive going edge and the negative going edge of the same channel.

Note 10: t_{SKD3} , Differential Part to Part Skew, is defined as the difference between the minimum and maximum specified differential propagation delays. This specification applies to devices at the same V_{DD} and within 5°C of each other within the operating temperature range.

Note 11: t_{SKD4}, part to part skew, is the differential channel to channel skew of any event between devices. This specification applies to devices over recommended operating temperature and voltage ranges, and across process distribution. t_{SKD4} is defined as IMax – MinI differential propagation delay.

Note 12: f_{MAX} generator input conditions: $t_r = t_f < 1$ ns (0% to 100%), 50% duty cycle, 0V to 3V. Output criteria: duty cycle = 45%/55%, V_{OD} > 250mV. The parameter is guaranteed by design. The limit is based on the statistical analysis of the device over the PVT range by the transitions times (t_{TLH} and t_{THL}).

Parameter Measurement Information



FIGURE 1. Differential Driver DC Test Circuit



FIGURE 2. Differential Driver Full Load DC Test Circuit





Parameter Measurement Information (Continued)





Application Information

Package Pin Number	Pin Name	Description	
SOT23	Fill Name	Description	
5	TTL IN	LVTTL/LVCMOS driver input pins	
4	OUT+	Non-inverting driver output pin	
3	OUT-	Inverting driver output pin	
2	GND	Ground pin	
1	V _{DD}	Power supply pin, +3.3V ± 0.3V	
	NC	No connect	

TABLE	1.	Device	Pin	Descriptions
IADEE		DCVICC		Descriptions



Leadfree products are RoHS compliant.



www.national.com

National Semiconductor Americas Customer Support Center Email: new.feedback@nsc.com Tel: 1-800-272-9959 National Semiconductor Europe Customer Support Center Fax: +49 (0) 180-530 85 86 Email: europe.support@nsc.com Deutsch Tel: +44 (0) 69 9508 6208 English Tel: +44 (0) 870 24 0 2171 Français Tel: +33 (0) 1 41 91 8790 National Semiconductor Asia Pacific Customer Support Center Email: ap.support@nsc.com National Semiconductor Japan Customer Support Center Fax: 81-3-5639-7507 Email: jpn.feedback@nsc.com Tel: 81-3-5639-7560 DS90LV011AH High Temperature 3V LVDS Differential Driver